# International **tor** Rectifier

Data Sheet No. PD60062 revP (NOTE:For new designs, we recommend IR's new product IRS2153D) IR2153(D)(S) &(PbF)

## SELF-OSCILLATING HALF-BRIDGE DRIVER

#### Features

- Integrated 600V half-bridge gate driver
- 15.6V zener clamp on Vcc
- True micropower start up
- Tighter initial deadtime control
- Low temperature coefficient deadtime
- Shutdown feature (1/6th Vcc) on C<sub>T</sub> pin
- Increased undervoltage lockout Hysteresis (1V)
- Lower power level-shifting circuit
- Constant LO, HO pulse widths at startup
- Lower di/dt gate driver for better noise immunity
- Low side output in phase with R⊤
- Internal 50nsec (typ.) bootstrap diode (IR2153D)
- Excellent latch immunity on all inputs and outputs
- ESD protection on all leads
- Also available LEAD-FREE

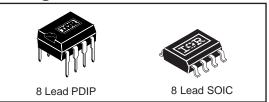
### Description

The IR2153D(S) are an improved version of the popular IR2155 and IR2151 gate driver ICs, and incor-

#### **Product Summary**

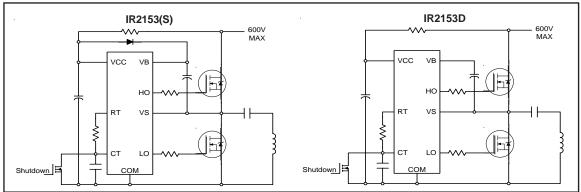
VOFFSET	600V max.
Duty Cycle	50%
Tr/Tp	80/40ns
V <sub>clamp</sub>	15.6V
Deadtime (typ.)	1.2 µs

#### Packages



porates a high voltage half-bridge gate driver with a front end oscillator similar to the industry standard CMOS 555 timer. The IR2153 provides more functionality and is easier to use than previous ICs. A shutdown feature has been designed into the C<sub>T</sub> pin, so that both gate driver outputs can be disabled using a low voltage control signal. In addition, the gate driver output pulse widths are the same once the rising undervoltage lockout threshold on V<sub>CC</sub> has been reached, resulting in a more stable profile of frequency vs time at startup. Noise immunity has been improved significantly, both by lowering the peak di/dt of the gate drivers, and by increasing the undervoltage lockout hysteresis to 1V. Finally, special attention has been payed to maximizing the latch immunity of the device, and providing comprehensive ESD protection on all pins.

## **Typical Connections**



#### IR2153(D)(S) & (PbF) NOTE:For new designs, we recommend

IR's new product IRS2153D

#### **Absolute Maximum Ratings**

Absolute maximum ratings indicate sustained limits beyond which damage to the device may occur. All voltage parameters are absolute voltages referenced to COM, all currents are defined positive into any lead. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions.

Symbol	Definition	Min.	Max.	Units	
VB	High side floating supply voltage		-0.3	625	
VS	High side floating supply offset voltage		V <sub>B</sub> - 25	V <sub>B</sub> + 0.3	
V <sub>HO</sub>	High side floating output voltage		V <sub>S</sub> - 0.3	V <sub>B</sub> + 0.3	
V <sub>LO</sub>	Low side output voltage		-0.3	V <sub>CC</sub> + 0.3	- V
V <sub>RT</sub>	R <sub>T</sub> pin voltage		-0.3	V <sub>CC</sub> + 0.3	
V <sub>CT</sub>	C <sub>T</sub> pin voltage		-0.3	V <sub>CC</sub> +0.3	
Icc	Supply current (note 1)		_	25	mA
I <sub>RT</sub>	R <sub>T</sub> pin current		-5	5	
dV <sub>s</sub> /dt	Allowable offset voltage slew rate		-50	50	V/ns
PD	Maximum power dissipation @ $T_A \le +25^{\circ}C$	(8 Lead DIP)	_	1.0	w
	(8 Lead SOIC)		_	0.625	· vv
RthJA	A Thermal resistance, junction to ambient (8 Lead DIP)		_	125	°C/W
	(8 Lead SOIC)		_	200	C/VV
Tj	Junction temperature		-55	150	
Τ <sub>S</sub>	Storage temperature		-55	150	°C
ΤL	Lead temperature (soldering, 10 seconds)		_	300	

#### **Recommended Operating Conditions**

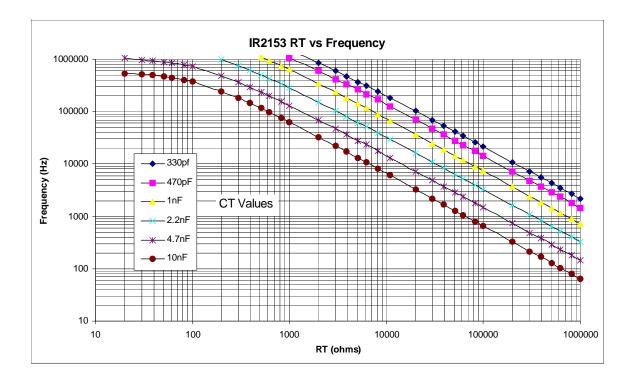
For proper operation the device should be used within the recommended conditions.

Symbol	Definition	Min.	Max.	Units
V <sub>Bs</sub>	High side floating supply voltage	V <sub>CC</sub> - 0.7	VCLAMP	
Vs	Steady state high side floating supply offset voltage	-3.0 (note 2)	600	V
Vcc	Supply voltage	10	VCLAMP	
Icc	Supply current	(note 3)	5	mA
Tj	Junction temperature	-40	125	°C

- Note 1: This IC contains a zener clamp structure between the chip V<sub>CC</sub> and COM which has a nominal breakdown voltage of 15.6V. Please note that this supply pin should not be driven by a DC, low impedance power source greater than the V<sub>CLAMP</sub> specified in the Electrical Characteristics section.
- Note 2: Care should be taken to avoid output switching conditions where the V<sub>S</sub> node flies inductively below ground by more than 5V.
- Note 3: Enough current should be supplied to the V<sub>CC</sub> pin of the IC to keep the internal 15.6V zener diode clamping the voltage at this pin.

#### **Recommended Component Values**

Symbol	Component	Min.	Max.	Units
R <sub>T</sub>	Timing resistor value	10	_	kΩ
CT	C <sub>T</sub> pin capacitor value	330	_	pF



#### IR2153(D)(S) & (PbF) NOTE:For new designs, we recommend

#### **Electrical Characteristics**

 $V_{BIAS}$  (V<sub>CC</sub>, V<sub>BS</sub>) = 12V, C<sub>L</sub> = 1000 pF, C<sub>T</sub> = 1 nF and T<sub>A</sub> = 25°C unless otherwise specified. The V<sub>IN</sub>, V<sub>TH</sub> and I<sub>IN</sub> parameters are referenced to COM. The V<sub>O</sub> and I<sub>O</sub> parameters are referenced to COM and are applicable to the respective output leads: HO or LO.

Low Voltage Supply Characteristics						
Symbo	Definition	Min.	Тур.	Max.	Units	Test Conditions
V <sub>CCUV+</sub>	Rising V <sub>CC</sub> undervoltage lockout threshold	8.1	9.0	9.9		
V <sub>CCUV</sub> -	Falling V <sub>CC</sub> undervoltage lockout threshold	7.2	8.0	8.8	V	
VCCUVH	V <sub>CC</sub> undervoltage lockout Hysteresis	0.5	1.0	1.5	1	
IQCCUV	Micropower startup V <sub>CC</sub> supply current	_	75	150		V <sub>CC</sub> ≤V <sub>CCUV</sub> -
locc	Quiescent V <sub>CC</sub> supply current	_	500	950	μΑ	
VCLAMP	V <sub>CC</sub> zener clamp voltage	14.4	15.6	16.8	V	$I_{CC} = 5mA$
Floati	ng Supply Characteristics					
Symbo	D Definition	Min.	Тур.	Max.	Units	Test Conditions
IQBSUV	Micropower startup VBS supply current	_	0	10		VCC ≤ VCCUV-
IQBS	Quiescent VBS supply current	_	30	50	μΑ	
VBSMIN	Minimum required V <sub>BS</sub> voltage for proper	_	4.0	5.0	V	V <sub>CC</sub> =V <sub>CCUV+</sub> + 0.1V
	functionality from R <sub>T</sub> to HO					
				50	μA	$V_{\rm B} = V_{\rm S} = 600 V$
ILK	Offset supply leakage current	-		50	μΑ	NB - NS - 000 N
I <sub>LK</sub> VF	Bootstrap diode forward voltage (IR2153D)	0.5		1.2	V	IF = 250mA
∨⊧ Oscilla	Bootstrap diode forward voltage (IR2153D)	 0.5 Min.	  Typ.	1.2		
∨⊧ Oscilla Symbo	Bootstrap diode forward voltage (IR2153D) tor I/O Characteristics I Definition	Min.		1.2 Max.	V	IF = 250mA Test Conditions
∨⊧ Oscilla	Bootstrap diode forward voltage (IR2153D)	<b>Min.</b> 19.4	20	1.2 Max. 20.6	V	IF = 250mA Test Conditions $R_T = 36.9k\Omega$
∨⊧ Oscilla Symbo	Bootstrap diode forward voltage (IR2153D)         ator I/O Characteristics         I Definition         Oscillator frequency	Min.		1.2 Max.	V	IF = 250mA Test Conditions
VF <b>Dscilla</b> Symbo f <sub>osc</sub> d	Bootstrap diode forward voltage (IR2153D)         ator I/O Characteristics         I Definition         Oscillator frequency         RT pin duty cycle	<b>Min.</b> 19.4 94	20 100	1.2 Max. 20.6 106	V Units kHz	IF = 250mA Test Conditions $R_T = 36.9k\Omega$ $RT = 7.43k\Omega$
VF Dscilla Symbo f <sub>osc</sub> d I <sub>CT</sub>	Bootstrap diode forward voltage (IR2153D)         ator I/O Characteristics         I Definition         Oscillator frequency	<b>Min.</b> 19.4 94 48	20 100 50	1.2 Max. 20.6 106 52	V Units kHz %	IF = 250mA <b>Test Conditions</b> $R_{T} = 36.9kΩ$ RT = 7.43kΩ fo < 100kHz
VF Dscilla Symbo fosc d I <u>CT</u> ICTUV	Bootstrap diode forward voltage (IR2153D)         ator I/O Characteristics         I Definition         Oscillator frequency         RT pin duty cycle         CT pin current	<b>Min.</b> 19.4 94 48 —	20 100 50 0.001	1.2 Max. 20.6 106 52 1.0	V Units kHz % uA	IF = 250mA Test Conditions $R_T = 36.9k\Omega$ $RT = 7.43k\Omega$
VF <b>Oscilla</b> Symbo f <sub>osc</sub> d	Bootstrap diode forward voltage (IR2153D)         ator I/O Characteristics         I Definition         Oscillator frequency         RT pin duty cycle         CT pin current         UV-mode CT pin pulldown current	<b>Min.</b> 19.4 94 48 —	20 100 50 0.001 0.70	1.2 Max. 20.6 106 52 1.0	V Units kHz % uA	IF = 250mA <b>Test Conditions</b> $R_{T} = 36.9kΩ$ RT = 7.43kΩ fo < 100kHz
VF <b>Oscilla</b> <b>Symbo</b> fosc d I <u>CT</u> I <u>CTUV</u> VCT+	Bootstrap diode forward voltage (IR2153D)         tor I/O Characteristics         I Definition         Oscillator frequency         RT pin duty cycle         CT pin current         UV-mode CT pin pulldown current         Upper CT ramp voltage threshold	<b>Min.</b> 19.4 94 48 —	20 100 50 0.001 0.70 8.0	1.2 <b>Max.</b> 20.6 106 52 1.0 1.2 —	V Units kHz % uA mA	IF = 250mA <b>Test Conditions</b> $R_{T} = 36.9kΩ$ RT = 7.43kΩ fo < 100kHz
VF Dscilla Symbo fosc d lct lctuv Vct+ Vct-	Bootstrap diode forward voltage (IR2153D)         ator I/O Characteristics         I Definition         Oscillator frequency         RT pin duty cycle         CT pin current         UV-mode CT pin pulldown current         Upper CT ramp voltage threshold         Lower CT ramp voltage threshold	Min. 19.4 94 48  0.30  	20 100 50 0.001 0.70 8.0 4.0	1.2 Max. 20.6 106 52 1.0 1.2  	V Units kHz % uA mA	IF = 250mA <b>Test Conditions</b> $R_{T} = 36.9kΩ$ RT = 7.43kΩ fo < 100kHz
VF Dscilla Symbo fosc d lct lct Uct Vct+ Vct- Vct- VctsD	Bootstrap diode forward voltage (IR2153D)         ator I/O Characteristics         I Definition         Oscillator frequency         RT pin duty cycle         CT pin current         UV-mode CT pin pulldown current         Upper CT ramp voltage threshold         Lower CT ramp voltage threshold         CT voltage shutdown threshold	Min. 19.4 94 48  0.30  	20 100 50 0.001 0.70 8.0 4.0 2.1	1.2 <b>Max.</b> 20.6 106 52 1.0 1.2  2.4	V Units kHz % uA mA	$IF = 250 \text{mA}$ $Test Conditions$ $R_T = 36.9 \text{k}\Omega$ $RT = 7.43 \text{k}\Omega$ fo < 100 kHz $V_{CC} = 7 \text{V}$
VF Oscilla Symbo fosc d lcT lcTUV VCT+ VCT- VCTSD	Bootstrap diode forward voltage (IR2153D)         ator I/O Characteristics         I Definition         Oscillator frequency         RT pin duty cycle         CT pin current         UV-mode CT pin pulldown current         Upper CT ramp voltage threshold         Lower CT ramp voltage threshold         CT voltage shutdown threshold	Min. 19.4 94 48  0.30  	20 100 50 0.001 0.70 8.0 4.0 2.1 10	1.2 <b>Max.</b> 20.6 106 52 1.0 1.2  2.4 50	V Units kHz % uA mA	IF = 250mA Test Conditions R <sub>T</sub> = 36.9kΩ RT = 7.43kΩ fo < 100kHz V <sub>CC</sub> = 7V I <sub>RT</sub> = 100μA
VF <b>Dscilla</b> <b>Symbo</b> fosc d ICT ICTUV VCT+ VCT- VCTSD VRT+	Bootstrap diode forward voltage (IR2153D)         ator I/O Characteristics         I Definition         Oscillator frequency         RT pin duty cycle         CT pin current         UV-mode CT pin pulldown current         Upper CT ramp voltage threshold         Lower CT ramp voltage threshold         CT voltage shutdown threshold         High-level RT output voltage, VCC - VRT	Min. 19.4 94 48  0.30  	20 100 50 0.001 0.70 8.0 4.0 2.1 10 100	1.2 <b>Max.</b> 20.6 106 52 1.0 1.2  2.4 50 300	V Units kHz % uA mA V	$IF = 250 \text{mA}$ $Test Conditions$ $R_T = 36.9 \text{k}\Omega$ $R_T = 7.43 \text{k}\Omega$ fo < 100 kHz $V_{CC} = 7 \text{V}$ $I_{RT} = 100 \mu \text{A}$ $I_{RT} = 1 \text{mA}$
VF <b>Dscilla</b> <b>Symbo</b> fosc d ICT ICTUV VCT+ VCT- VCTSD VRT+	Bootstrap diode forward voltage (IR2153D)         ator I/O Characteristics         I Definition         Oscillator frequency         RT pin duty cycle         CT pin current         UV-mode CT pin pulldown current         Upper CT ramp voltage threshold         Lower CT ramp voltage threshold         CT voltage shutdown threshold         High-level RT output voltage, VCC - VRT	Min. 19.4 94 48  0.30  	20 100 50 0.001 0.70 8.0 4.0 2.1 10 100 10	Max.           20.6           106           52           1.0           1.2              2.4           50           300           50	V Units kHz % uA mA	$IF = 250 \text{mA}$ $Test Conditions$ $R_T = 36.9 \text{k}\Omega$ $RT = 7.43 \text{k}\Omega$ fo < 100 \text{kHz} $V_{CC} = 7 \text{V}$ $I_{RT} = 100 \mu \text{A}$ $I_{RT} = 1 \text{mA}$ $I_{RT} = 100 \mu \text{A}$
VF Oscilla Symbo fosc d ICT ICTUV VCT+ VCT- VCTSD VRT+ VRT-	Bootstrap diode forward voltage (IR2153D)         ator I/O Characteristics         I Definition         Oscillator frequency         RT pin duty cycle         CT pin current         UV-mode CT pin pulldown current         Upper CT ramp voltage threshold         Lower CT ramp voltage threshold         High-level RT output voltage         Low-level RT output voltage	Min. 19.4 94 48  0.30  	20 100 50 0.001 0.70 8.0 4.0 2.1 10 100 10 100	1.2 Max. 20.6 106 52 1.0 1.2  2.4 50 300 50 300	V Units kHz % uA mA V	$IF = 250 \text{mA}$ $Test Conditions$ $R_T = 36.9 \text{k}\Omega$ $RT = 7.43 \text{k}\Omega$ fo < 100 \text{kHz} $V_{CC} = 7 \text{V}$ $I_{RT} = 100 \mu \text{A}$
VF Oscilla Symbo fosc d ICT ICTUV VCT+ VCT+ VCTSD VRT+ VRT- VRT-	Bootstrap diode forward voltage (IR2153D)         ator I/O Characteristics         I Definition         Oscillator frequency         RT pin duty cycle         CT pin current         UV-mode CT pin pulldown current         Upper CT ramp voltage threshold         Lower CT ramp voltage threshold         High-level RT output voltage         UV-mode RT output voltage	Min. 19.4 94 48  0.30  1.8  1.8       	20 100 50 0.001 0.70 8.0 4.0 2.1 10 100 10 100 0	Max.           20.6           106           52           1.0           1.2              2.4           50           300           50           300           100	V Units kHz % uA mA V	$IF = 250 \text{mA}$ $Test Conditions$ $R_T = 36.9 \text{k}\Omega$ $RT = 7.43 \text{k}\Omega$ fo < 100 kHz $V_{CC} = 7 \text{V}$ $I_{RT} = 100 \mu \text{A}$ $I_{RT} = 1 \text{mA}$ $I_{RT} = 100 \mu \text{A}$ $I_{RT} = 1 \text{mA}$ $V_{CC} \leq V_{CCUV}$

 $V_{CT} = 0V$ 

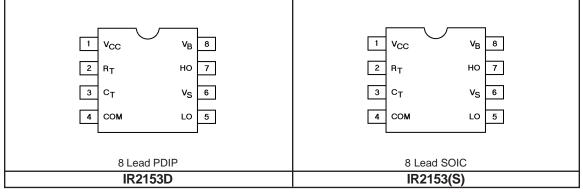
### **Electrical Characteristics (cont.)**

Gate Driver Output Characteristics						
Symbol	Definition	Min.	Тур.	Max.	Units	<b>Test Conditions</b>
VOH	High level output voltage, V <sub>BIAS</sub> -V <sub>O</sub>	—	0	100		I <sub>O</sub> = OA
VOL	Low-level output voltage, VO	_	0	100	mV	I <sub>O</sub> = OA
VOL_UV	UV-mode output voltage, VO		0	100		I <sub>O</sub> = OA
						V <sub>CC</sub> ≤V <sub>CCUV</sub> -
tr	Output rise time		80	150		
tf	Output fall time	_	45	100	nsec	
t <sub>sd</sub>	Shutdown propogation delay	—	660	—	1	
td	Output deadtime (HO or LO)	0.75	1.20	1.65	μsec	

#### **Lead Definitions**

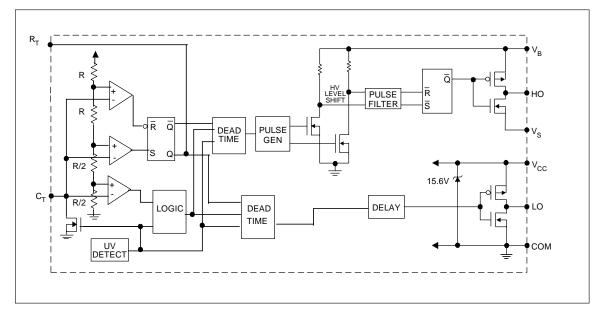
Symbol	Description
Vcc	Logic and internal gate drive supply voltage
R <sub>T</sub>	Oscillator timing resistor input
CT	Oscillator timing capacitor input
COM	IC power and signal ground
LO	Low side gate driver output
Vs	High voltage floating supply return
НО	High side gate driver output
VB	High side gate driver floating supply

#### Lead Assignments

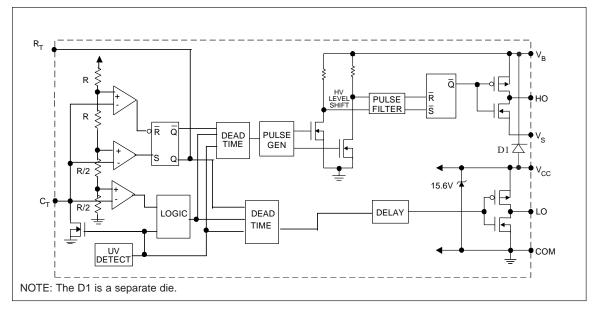


NOTE: The IR2153D is offered in 8 lead PDIP only.

### Functional Block Diagram for IR2153(S)



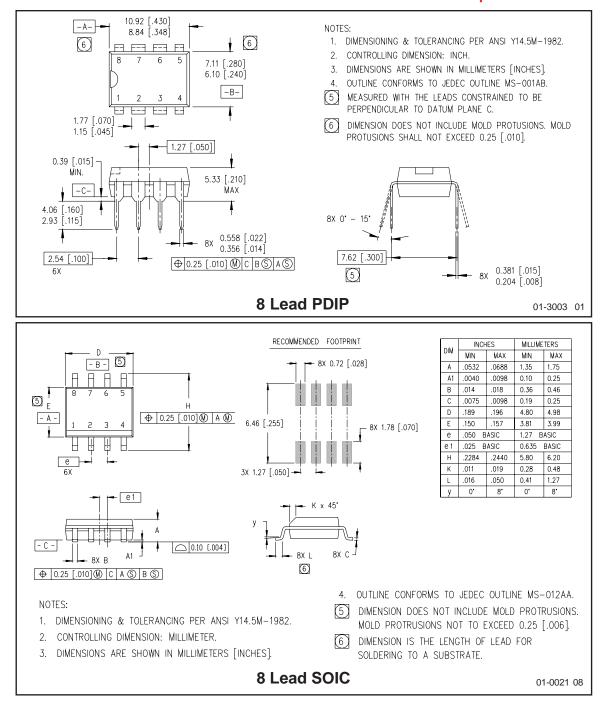
### Functional Block Diagram for IR2153D



# International

## IR2153(D)(S)& (PbF)

NOTE:For new designs, we recommend IR's new product IRS2153D



#### IR2153(D)(S) & (PbF) NOTE:For new designs, we recommend IR's new product IRS2153D

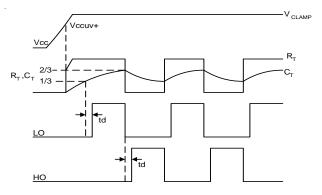


Figure 1. Input/Output Timing Diagram

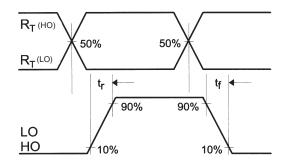


Figure 2. Switching Time Waveform Definitions

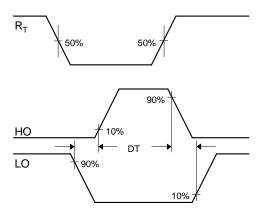
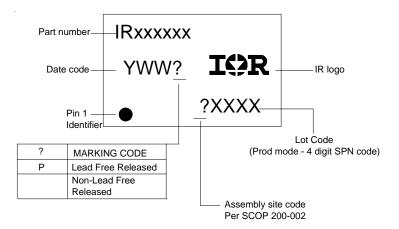


Figure 3. Deadtime Waveform Definitions

### LEADFREE PART MARKING INFORMATION



### **ORDER INFORMATION**

#### **Basic Part (Non-Lead Free)**

8-Lead PDIP IR2153 order IR2153 8-Lead SOIC IR2153S order IR2153S 8-Lead PDIP IR2153D order IR2153D

#### Leadfree Part

8-Lead PDIP IR2153 order IR2153PbF 8-Lead SOIC IR2153S order IR2153SPbF 8-Lead PDIP IR2153D order IR2153DPbF

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